

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1272	dmos and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:31
L2	67	dmos and cmos and (low adj concentration) and (high adj concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:36
L3	272	dmos and cmos and (ldd or (lightly adj doped adj drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:38
L4	166	dmos and cmos and (ldd or (lightly adj doped adj drain)) and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:38
L5	25	dmos and cmos and (ldd or (lightly adj doped adj drain)) and embedded	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:39
L6	1	dmos and cmos and (ldd or (lightly adj doped adj drain)) and encapsulated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:40
L7	226	dmos and cmos and controller	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:40
L8	1	dmos and cmos and (fixed adj voltage adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:41

## EAST Search History

L9	96	dmos and cmos and (output adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:42
L10	597	dmos and cmos and conductivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:42
L11	244	dmos and cmos and polarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 14:43